
2SK2959

Silicon N Channel MOS FET
High Speed Power Switching

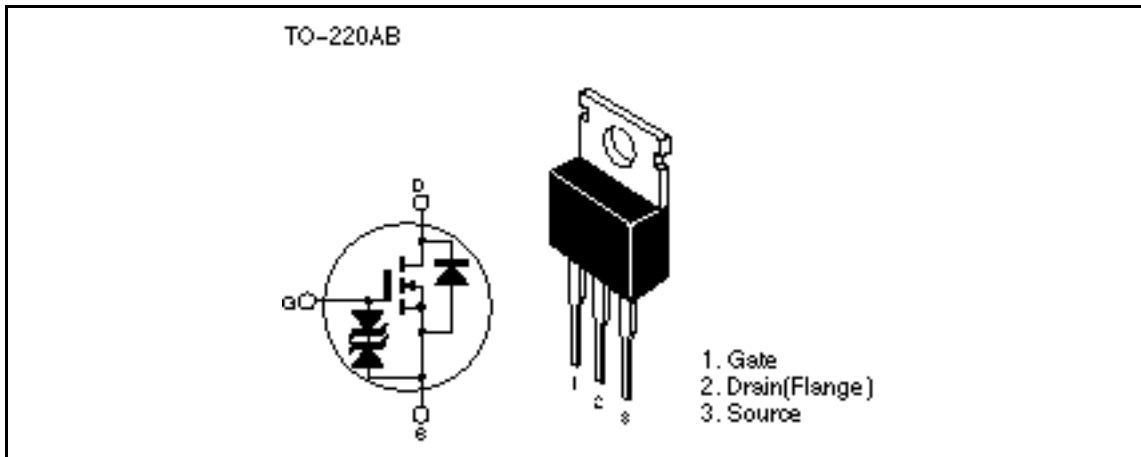
HITACHI

ADE-208-569
Target specification 1st. Edition

Features

- Low on-resistance
 $R_{DS(on)} = 7m \text{ typ.}$
- 4V gate drive devices.
- High speed switching

Outline



2SK2959

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	50	A
Drain peak current	$I_{D(pulse)}^{*1}$	200	A
Body to drain diode reverse drain current	I_{DR}	50	A
Channel dissipation	Pch ^{*2}	75	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

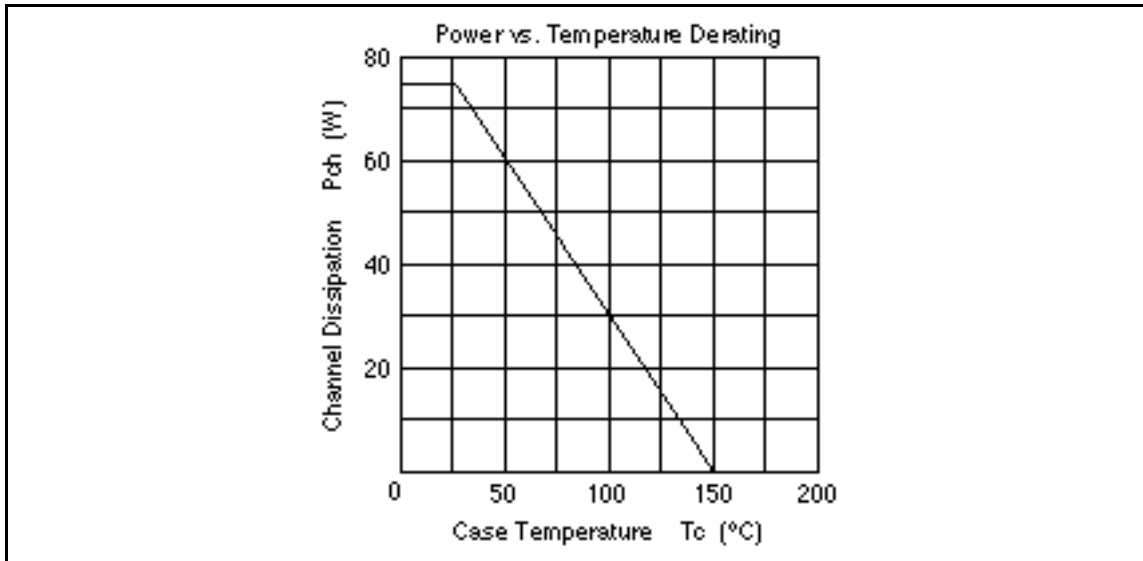
Notes: 1. PW = 10µs, duty cycle = 1 %
 2. Value at Tc = 25°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	$I_D = 10mA, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = ±100µA, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	µA	$V_{DS} = 30V, V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	µA	$V_{GS} = ±16V, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1mA, V_{DS} = 10V$
Static drain to source on state resistance	$R_{DS(on)}$	—	7.0	10	m	$I_D = 25A, V_{GS} = 10V^{*1}$
	$R_{DS(on)}$	—	12	18	m	$I_D = 25A, V_{GS} = 4V^{*1}$
Forward transfer admittance	$ y_{fs} $	25	45	—	S	$I_D = 25A, V_{DS} = 10V^{*1}$
Input capacitance	Ciss	—	2000	—	pF	$V_{DS} = 10V$
Output capacitance	Coss	—	1500	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	—	350	—	pF	f = 1MHz
Turn-on delay time	$t_{d(on)}$	—	20	—	ns	$V_{GS} = 10V, I_D = 25A$
Rise time	t_r	—	330	—	ns	$R_L = 0.4$
Turn-off delay time	$t_{d(off)}$	—	190	—	ns	
Fall time	t_f	—	190	—	ns	
Body to drain diode forward voltage	V_{DF}	—	0.95	—	V	$I_D = 50A, V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	140	—	ns	$I_F = 50A, V_{GS} = 0$ diF/ dt = 50A/µs

Note: 1. Pulse test

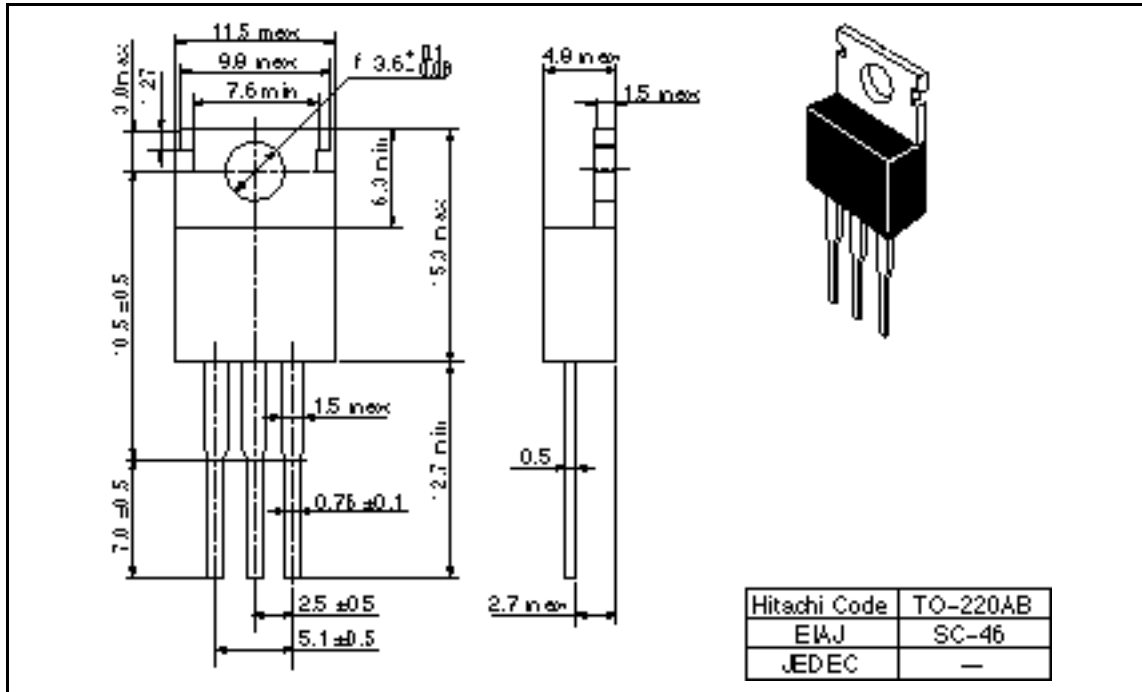
Main Characteristics



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Package Dimensions

Unit: mm



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